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for copper intercon: oct grown by electrochemical displacement

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AMENDMENTS TO THE CLAIMS

The following listing of claims will replace all prior versions, and listing of claims in the application:

LISTING OF CLAIMS:

Claim: (Currently amended) At: A method for forming copper interconnects including an oxygen-removing pre-process, the method comprising ine steps of:

providing a solvent;

b. heating the solvent to a boil in an open container and maintaining the boiling condition for a predetermined time period to remove dissolved exygen therefrom.

cooling the solvern

ci.

c. forming a reaction solution by mixing hydrofluoric scid and cupric sulfate with the ocolec solven::

c. preparing a substrate with a Ti metal displacement

solution to carry out a displacement process for forming a copper-

iln layer.

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polypropylene film to isolate the solvent from exposure to air.

MR1683-507 Sarial Mucher: 10/716,550 Reply to Ufficial Action dated 5 April 2004 deposition is to remove the exagen in the reaction-sol

deposition is to remove the exygen in the reaction solution before displacement and deposition—a copper film—feunducting wire such that the copper film-enducting wire is grown and has a lower electric resistance.

Claim 2 (Cancelled).

Cleim 3 (Currently amended) The exygen removing pre-process method as plaimed in claim [[2]] L. wherein the exygen in the reaction solution is remeved by being boiled step of maintaining the boiling condition for a predetermined time includes the step of beiling the solvent for two minutes.

Claim 4 (Currently amended) The oxygen-removing pre-process method as claimed in claim 3, wherein the recetion solution is easiered step of cooling includes covering the container to prevent the ambient oxygen in the air from being dissolved into the reaction solution decing cooling.

Claim 5 (Currently amended) The exygen removing pre-process muthod as claimed in claim 4, wherein the steep of a centainer for receiving the recution solution received in the container covering the container includes the step of covering the container with

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MR1683-307 Serial Number: 10-716,550 Reply to Official Action dated 5 April 3092 Claim 6 (Currently amended) The nethod as caimed in claim 1.

wherein the step of providing a solvent includes the step of providing deionized

water. An oxygen removing pre-greeess for electrochemical displacement
deposition removing oxygen in the rescion solution by boring, the reaction
solution insulated to prevent the oxygen in the air form heing dissolved into the
reaction solution during cooling, the reaction solution mixed with liquid and
provided to the electrochemical displacement deposition for reducing the
electric resistance of the grown copper.

Claim 7 (Currently amended) The exygen removing pre-process method as claimed in claim 6, wherein the step of forming a reaction solution is mixed with deionized water includes mixing forty-millilitum of a buffered hydrofluoric seid and four-grams of cupic sulphate mixed in one liter of the deionized water.

Claims 8 - 9 (Cance..ed).

Claim 10 (Currently amended) The <u>method</u> oxygen removing preprecess as claimed in claim 6.4, wherein the <u>step of cooling includes the step of</u> <u>cooling the solvent reaction-solution cools</u> for forty minutes.

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Claims 11 - 12 (Cancelled).

Claim 13 (Currently amended) The exygen removing pre-process method as claimed in claim 6.1, wherein the step of forming a Ti metal displacement layer is previously formed on the wafer by includes forming the Ti metal displacement layer with a sputtering system.

Claim 14 (Corroudy amended). The exygen removing pre-process method as claimed in claim 13, wherein the T. metal displacement layer formed has a thickness for of 3000 Å.

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